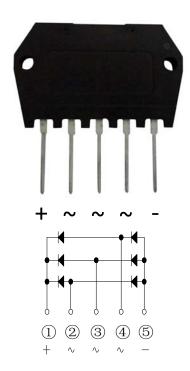




Three Phase Bridge Rectifiers



Features

- UL recognition, file #E230084
- Glass passivated chip junction
- Thin single in-line package
- High surge current capability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

General purpose use in AC/DC bridge full wave rectification for switching power supply, home appliances, office equipment, industrial automation applications.

Mechanical Data

• Package: TSB-5

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

• Polarity: As marked on body

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	DF25NA80	DF25NA100	DF25NA120	DF25NA160
Device marking code			DF25NA80	DF25NA100	DF25NA120	DF25NA160
Maximum Repetitive Peak Reverse Voltage	VRRM	V	800	1000	1200	1600
Maximum RMS Voltage	VRMS	V	560	700	840	1120
Maximum DC blocking Voltage	VDC	V	800	1000	1200	1600
Average Rectified Output Current @8.3ms, sine wave, R-load, With heatsink, $T_C = 115^{\circ}C$	IO	А	25			
Forward Surge Current (Non-repetitive) @8.3ms, Half-sine wave,1 cycle, Tj=25°C	l=o.4		400			
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25°C	IFSM A		800			
Current Squared Time @1ms≤t<8.3ms Tj=25℃,Rating of per diode	l²t	A ² S	664			
Dielectric strength @terminals to case, AC 1 minute	Vdis	KV	2.5			
Mounting torque @recommend torque: 5kg·cm	Tor	kg·cm	8			
Storage Temperature	T _{stg}	${\mathbb C}$	-55 ~ +150			
Junction Temperature	Tj	$^{\circ}$	-55 ~ +150			

DF25NA80 THRU DF25NA160

■Electrical Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	DF25NA80	DF25NA100	DF25NA120	DF25NA160
Maximum instantaneous forward voltage drop per diode	VF	V	IFM=12.5A	1.1			
Maximum DC reverse current at rated DC blocking voltage per diode IR μΑ			T _j =25°C	5			
		T _j =125°C	500				
Typical junction capacitance	Cj	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	23	30	24	40

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

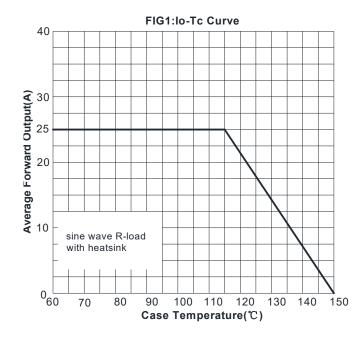
	PARAMETER	SYMBOL	UNIT	DF25NA80	DF25NA100	DF25NA120	DF25NA160
Thermal Resistance	Between junction and case, With heatsink	RøJ-C	°C/W		1.2	2	

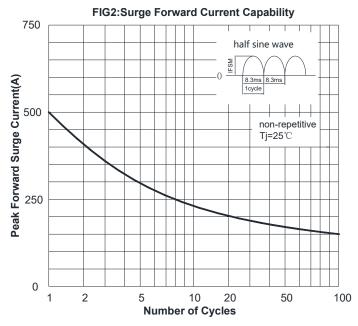
Note: Device mounted on 75mm x 45mm x 5.5mm Aluminum Plate Heatsink.

■Ordering Information (Example)

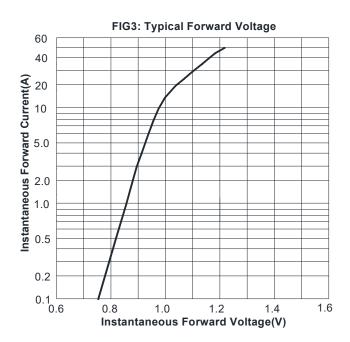
PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
DF25NA80 ~ DF25NA160	Approximate 15.8	96	96	576	Paper Box

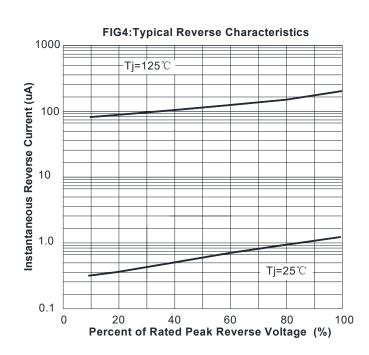
■ Characteristics(Typical)



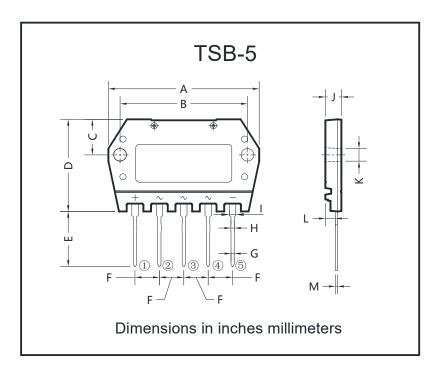


DF25NA80 THRU DF25NA160





■ Outline Dimensions



TSB-5						
Dim	Min	Max				
Α	46.6	47.6				
В	39.5	40.1				
С	11.0	11.6				
D	28.8	29.8				
Е	17.2	17.8				
F	7.52	7.72				
G	0.90	1.10				
Н	1.00	1.20				
ı	1.90	2.10				
J	4.70	5.30				
K	4.00	4.50				
L	3.00	3.20				
М	0.60	0.80				



DF25NA80 THRU DF25NA160

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